

# International IR Rectifier

PD - 91841A

## IRLBA3803/P

HEXFET® Power MOSFET

- Logic-Level Gate Drive
- Advanced Process Technology
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

### Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The Super-220 is a package that has been designed to have the same mechanical outline and pinout as the industry standard TO-220 but can house a considerably larger silicon die. It has increased current handling capability over both the TO-220 and the much larger TO-247 package.

This makes it ideal to reduce component count in multiparallel TO-220 applications, reduce system power dissipation, upgrade existing designs or have TO-247 performance in a TO-220 outline.

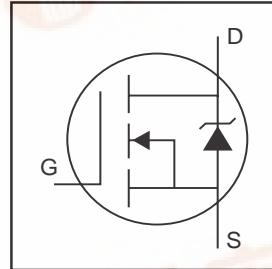
This package has also been designed to meet automotive qualification standard Q101.

### Absolute Maximum Ratings

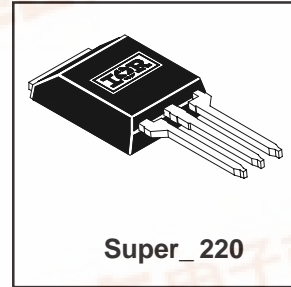
	Parameter	Max.	Units
$I_D$ @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	179 ⑥	A
$I_D$ @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	126 ⑥	
$I_{DM}$	Pulsed Drain Current ①	720	
$P_D$ @ $T_C = 25^\circ\text{C}$	Power Dissipation	270	W
	Linear Derating Factor	1.8	W/°C
$V_{GS}$	Gate-to-Source Voltage	±16	V
$E_{AS}$	Single Pulse Avalanche Energy ② ⑤	610	mJ
$I_{AR}$	Avalanche Current ① ⑤	71	A
$E_{AR}$	Repetitive Avalanche Energy ①	27	mJ
dv/dt	Peak Diode Recovery dv/dt ③ ⑤	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	
	Recommended clip force	20	N

### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.55	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.5	—	
$R_{\theta JA}$	Junction-to-Ambient	—	58	



$V_{DSS} = 30\text{V}$
$R_{DS(on)} = 0.005\Omega$
$I_D = 179\text{A} \text{ ⑥}$



## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.052	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}$ , $I_D = 1\text{mA}$ ⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.005	$\Omega$	$V_{GS} = 10V, I_D = 71A$ ④
		—	—	0.009		$V_{GS} = 4.5V, I_D = 59A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	55	—	—	S	$V_{DS} = 25V, I_D = 71A$ ⑤
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 30V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 24V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
$Q_g$	Total Gate Charge	—	—	140	nC	$I_D = 71A$
$Q_{gs}$	Gate-to-Source Charge	—	—	41		$V_{DS} = 24V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	78		$V_{GS} = 4.5V$ , See Fig. 6 and 13 ④⑤
$t_{d(on)}$	Turn-On Delay Time	—	14	—		$V_{DD} = 15V$
$t_r$	Rise Time	—	230	—		$I_D = 71A$
$t_{d(off)}$	Turn-Off Delay Time	—	29	—		$R_G = 1.3\Omega$
$t_f$	Fall Time	—	35	—		$R_D = 0.20\Omega$ , See Fig. 10 ④⑤
$L_D$	Internal Drain Inductance	—	2.0	—		nH
$L_S$	Internal Source Inductance	—	5.0	—		
$C_{ISS}$	Input Capacitance	—	5000	—	pF	$V_{GS} = 0V$
$C_{OSS}$	Output Capacitance	—	1800	—		$V_{DS} = 25V$
$C_{RSS}$	Reverse Transfer Capacitance	—	880	—		$f = 1.0\text{MHz}$ , See Fig. 5⑤

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	179⑥	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode)①	—	—	720		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 71A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	120	180	ns	$T_J = 25^\circ\text{C}, I_F = 71A$
$Q_{rr}$	Reverse Recovery Charge	—	450	680	nC	$di/dt = 100A/\mu s$ ④⑤
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ②  $V_{DD} = 15V$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 180\mu H$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 71A$ . (See Figure 12)
- ③  $I_{SD} \leq 71A$ ,  $di/dt \leq 130A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ\text{C}$

④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

⑤ Uses IRL3803 data and test conditions.

⑥ Calculated continuous current based on maximum allowable junction temperature; for recommended current-handling of the package refer to Design Tip # 93-4

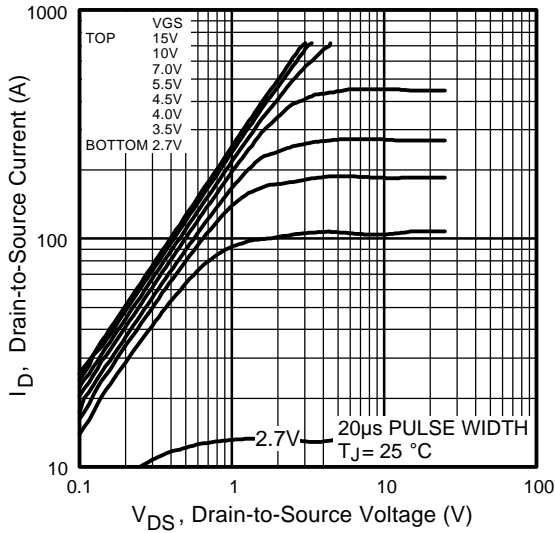


Fig 1. Typical Output Characteristics

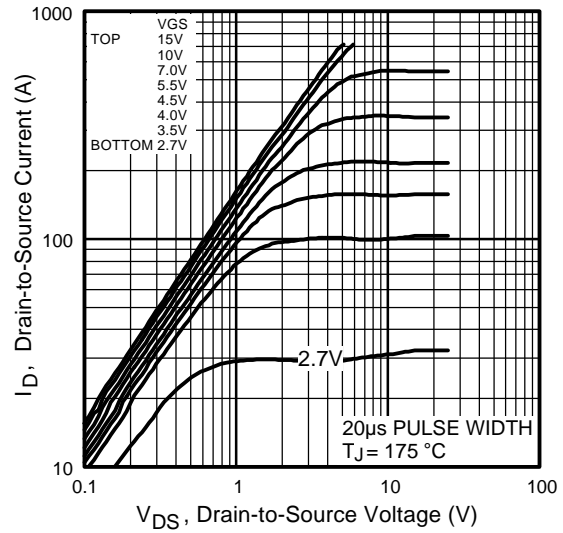


Fig 2. Typical Output Characteristics

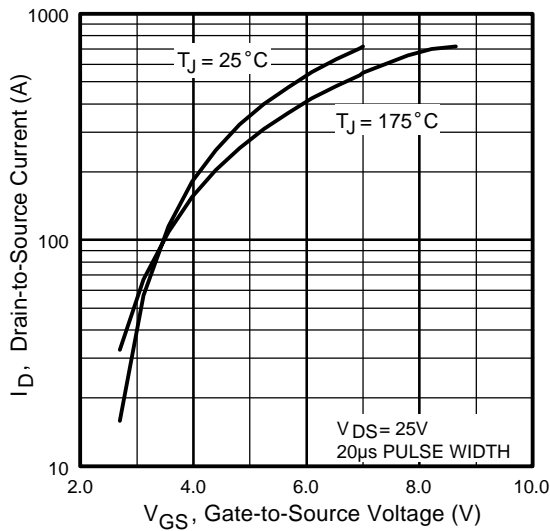


Fig 3. Typical Transfer Characteristics

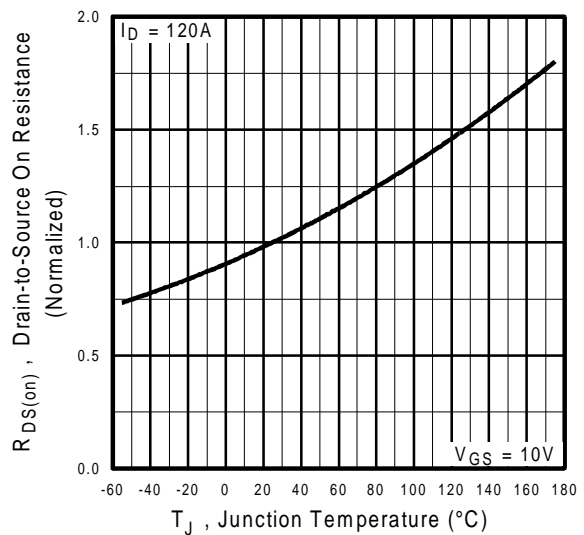
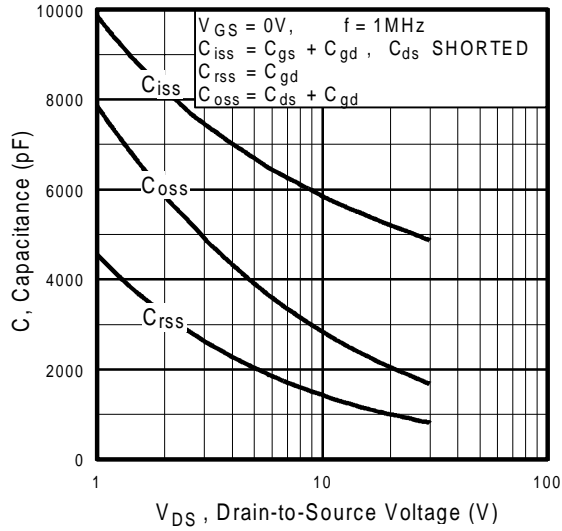
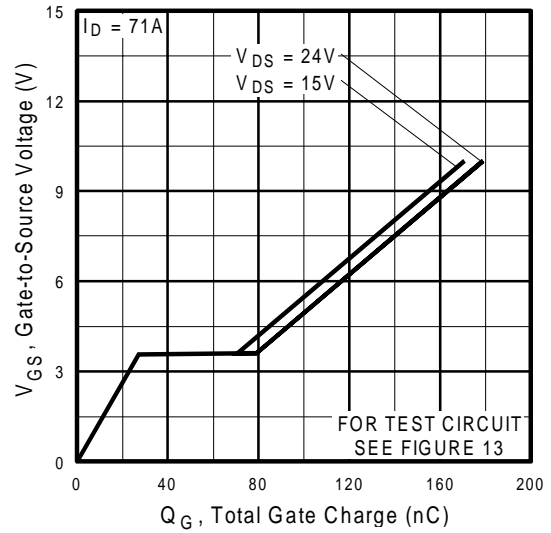


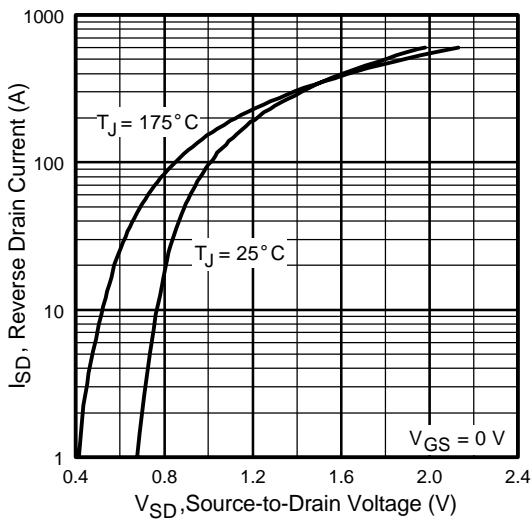
Fig 4. Normalized On-Resistance Vs. Temperature



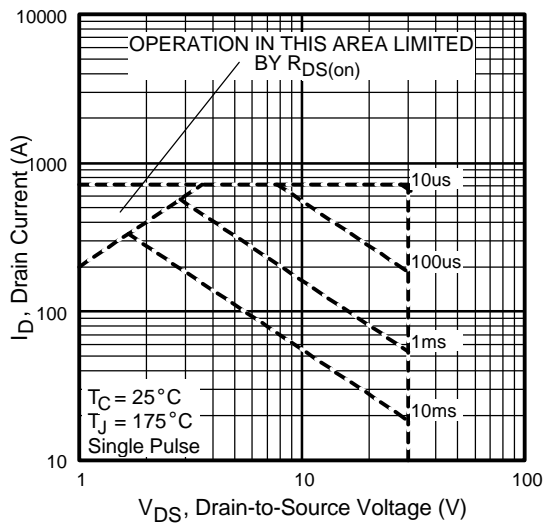
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

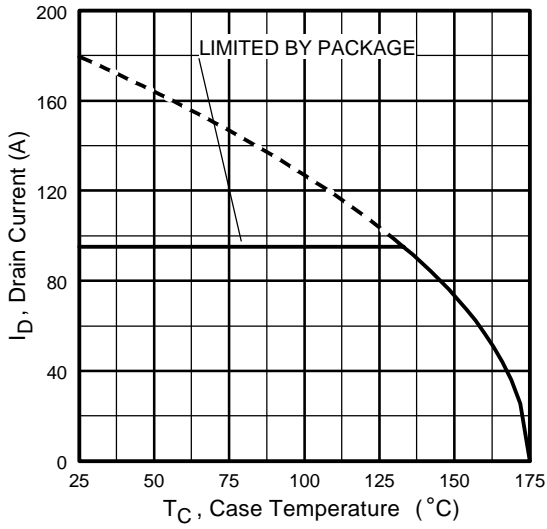


Fig 9. Maximum Drain Current Vs. Case Temperature

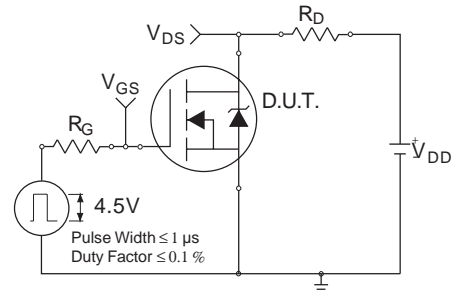


Fig 10a. Switching Time Test Circuit

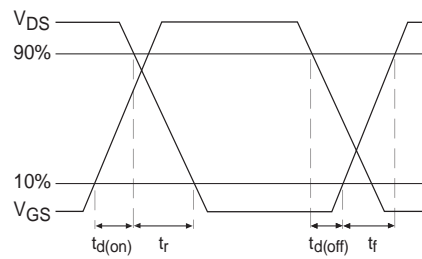


Fig 10b. Switching Time Waveforms

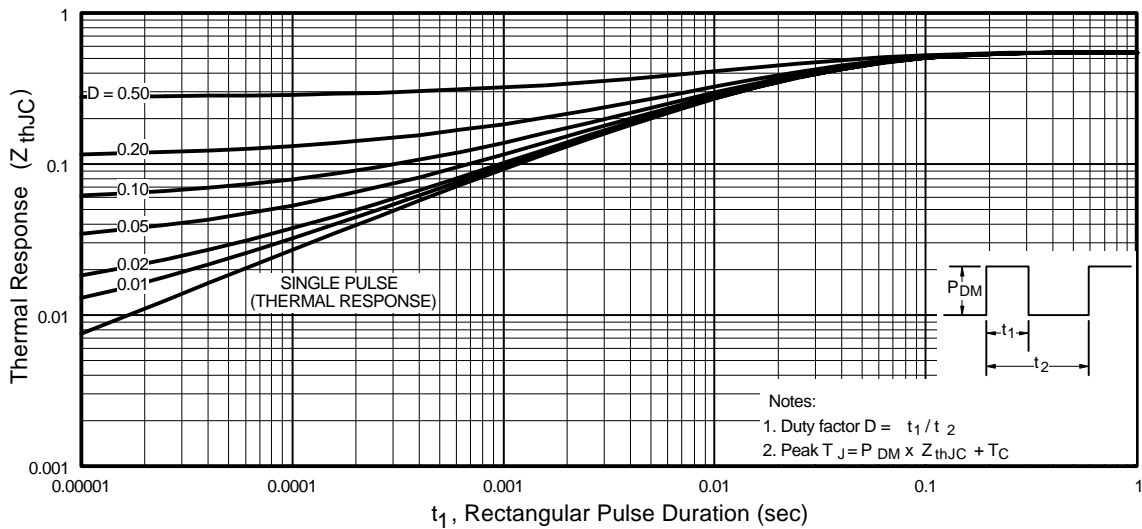


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

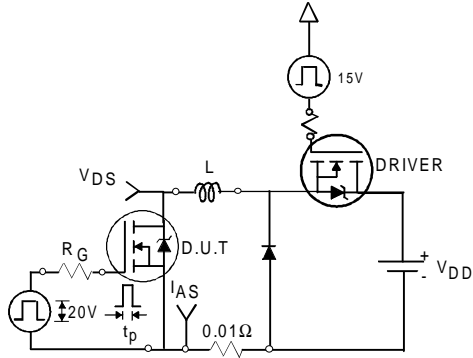


Fig 12a. Unclamped Inductive Test Circuit

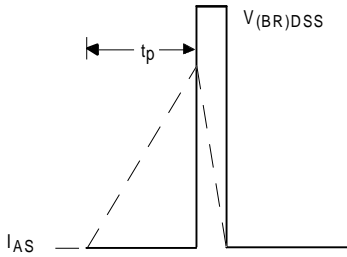


Fig 12b. Unclamped Inductive Waveforms

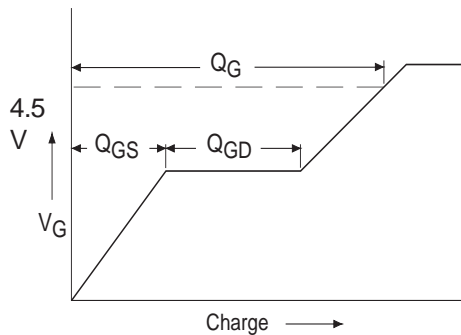


Fig 13a. Basic Gate Charge Waveform

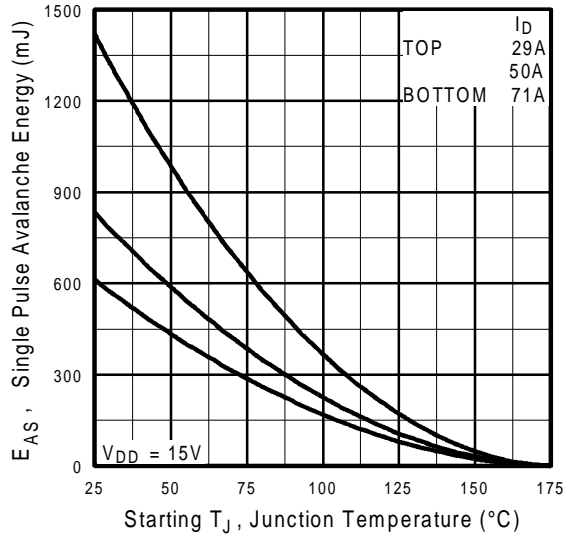


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

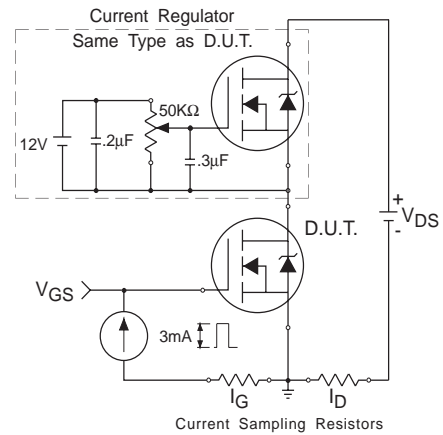
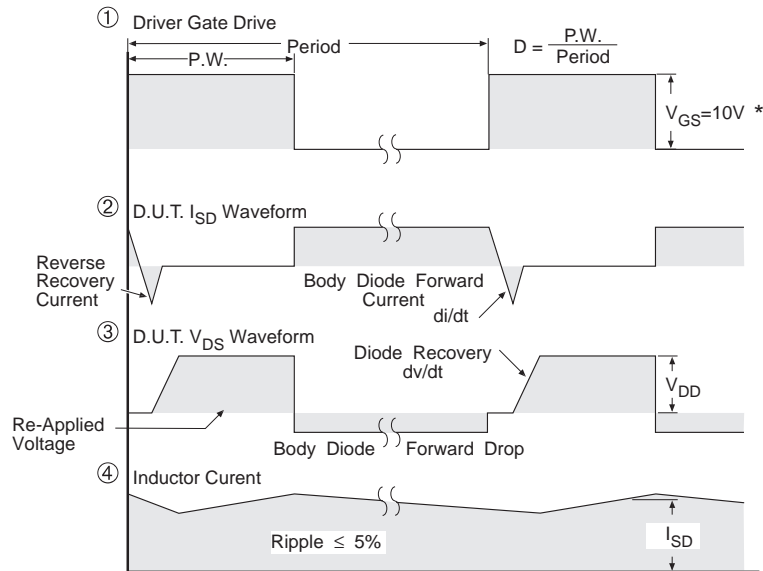
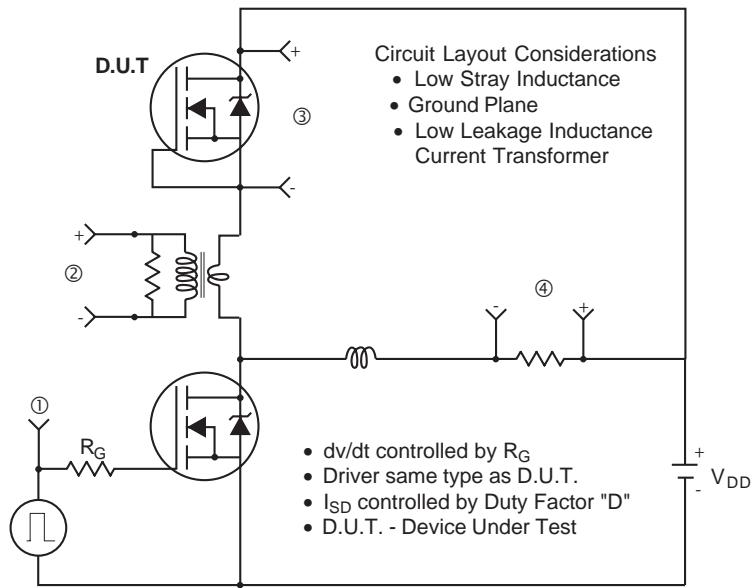


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



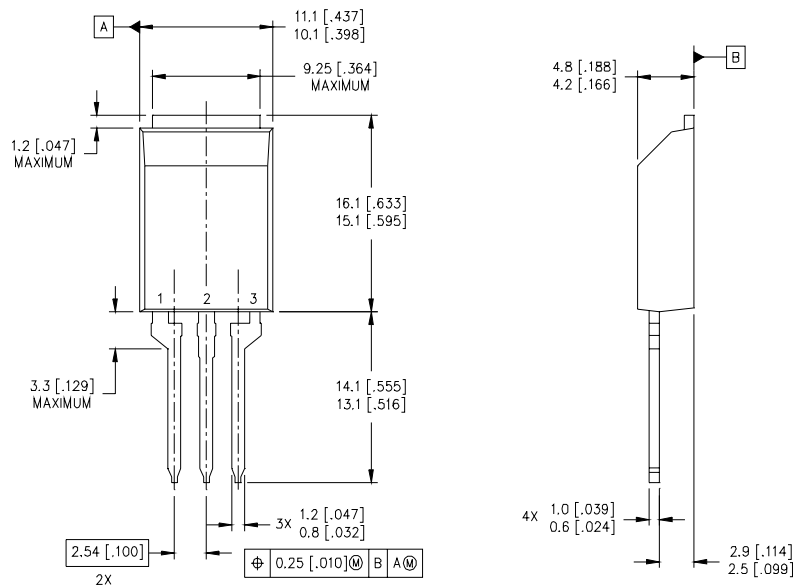
\*  $V_{GS} = 5V$  for Logic Level Devices

Fig 14. For N-Channel HEXFETS

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## Super\_220 Package Outline



### NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

International  
**IR** Rectifier

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Data and specifications subject to change without notice. 1/99